

IN THE CLAIMS:

1. (currently amended): Semiconductor laser chip having a semiconductor laser element, [[and a]] beam shaper integrated into the semiconductor laser chip and serving to shape a laser beam emitted by the semiconductor laser element, and a trench introduced between the semiconductor laser element and the beam shaper, the semiconductor laser element being configured as an FP semiconductor laser element, the beam shaper being arranged in a manner integrated in the semiconductor laser element in the exit direction of a laser beam emitted by the semiconductor laser element, such that the emitted laser beam is guided through the beam shaper, the beam shaper having a predetermined concentration profile of oxidized aluminium.

2. (original): Semiconductor laser chip according to Claim 1, in which the beam shaper is monolithically integrated in the semiconductor laser chip.

3. (previously amended) Semiconductor laser chip according to Claim 1, in which the beam shaper has aluminium-containing material.

B 4. (previously amended): Semiconductor laser chip according to Claim 3, in which the beam shaper has at least one material combination selected from the group consisting of indium gallium aluminium antimonide, gallium aluminium arsenide antimonide, and indium aluminium arsenide antimonide.

5. (currently amended) Semiconductor laser chip according to Claim 1, ~~in which a trench is introduced between the semiconductor laser element and the beam shaper~~ in which the trench has a width of at most 15  $\mu\text{m}$  between the edge of the semiconductor laser element from which the laser beam is emitted and the beam-input-end surface of the beam shaper.

6. Canceled.

7. Canceled.

8. Canceled.

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9. (currently amended): Method for fabricating a semiconductor laser chip, in which an FP semiconductor laser element is formed; comprising formation of a beam shaper in the exit direction of a laser beam emitted by the semiconductor laser element, in such a manner that the emitted laser beam is guided through the beam shaper, in which case, in order to form the beam shaper, a beam shaper region is formed in the exit direction of a laser beam emitted by the semiconductor laser element, the beam shaper region containing aluminium, a desired aluminium concentration profile is formed in the beam shaper region, a selective oxidation of the beam shaper region is carried out, such that the beam shaper is formed depending on the aluminium concentration profile, and a trench is introduced between the semiconductor laser element and the beam shaper region or the beam shaper.

10. (previously amended): Method according to Claim 9, further comprising at least one material combination of at least one of material system selected from the group consisting of indium gallium aluminium antimonide, gallium aluminium arsenide antimonide, and indium aluminium arsenide antimonide.

11. Canceled.

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